Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO220F-2L plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I_{FSM}
- · Extremely fast reverse recovery time
- · Superior in efficiency to Silicon Diode alternatives
- · Reduced losses in associated MOSFET
- Reduced EMI
- · Reduced cooling requirements
- RoHS compliant
- Insulated package rated at 2500V RMS

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Values			Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			6	50		V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; T _h ≤ 77 °C; Fig. 1; Fig. 2; Fig. 3	6			Α	
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V _F	forward voltage	I _F = 6 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.5	1.7	V
		I _F = 6 A; T _i = 150 °C; <u>Fig. 5</u>		-	1.8	2.1	V

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		1/ 1/4 A
2	Α	anode	O	K A 001aaa020
mb	n.c.	mounting base; isolated	1 2	

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
NXPSC06650X	TO220F-2L	NXPSC06650X6Q	Tube	50	TO220FN-2L	20-July-2016

7. Marking

Table 4. Marking codes

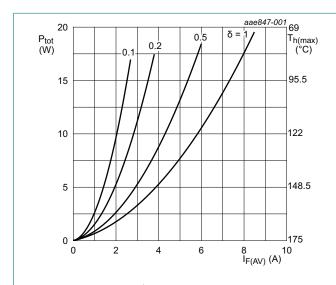
Type number	Marking codes
NXPSC06650X	NXPSC 06650X

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		650	V
V_{RWM}	crest working reverse voltage		650	V
V_R	reverse voltage	DC	650	V
I _{F(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_h \le 77$ °C; Fig. 1; Fig. 2; Fig. 3	6	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 77 °C$; square-wave pulse	12	А
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	36	А
	forward current	t _p = 10 μs; T _{j(init)} = 25 °C; square-wave pulse	310	А
l ² t	I ² t for fusing	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	6.48	A ² s
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 0.444 \text{ V; R}_s = 0.2192 \text{ }\Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

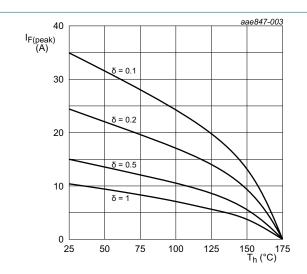
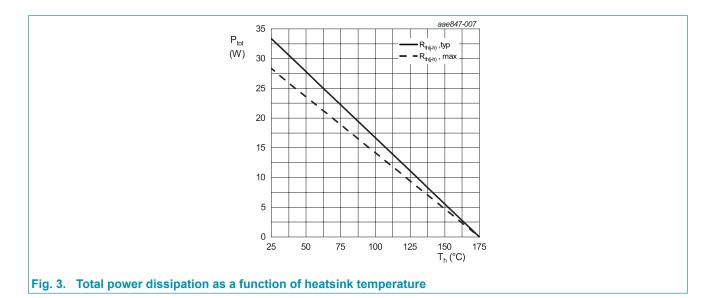


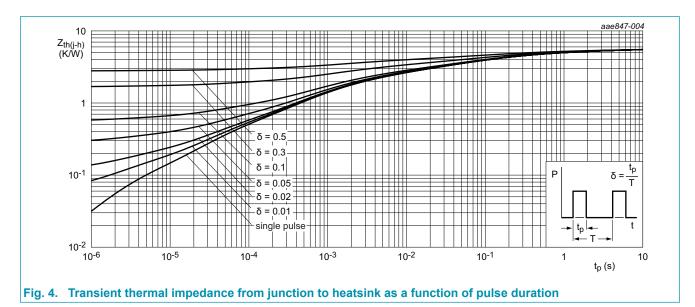
Fig. 2. Current derating as a function of heatsink temperature



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig. 4		-	4.5	5.3	K/W
$R_{\text{th(j-a)}}$	thermal resistance in free air from junction to ambient free air			-	55	-	K/W



10. Isolation characteristics

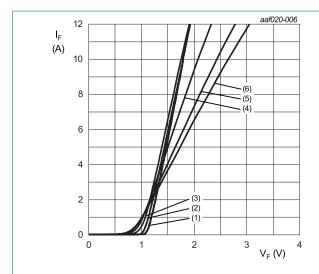
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; T _h = 25 °C; RH \leq 65 %	-	-	2500	V

11. Characteristics

Table 8 Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	aracteristics						
V_{F}	forward voltage	I _F = 6 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.5	1.7	V
		I _F = 6 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.8	2.1	V
I _R reverse current	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>		-	-	40	μA
		V _R = 650 V; T _j = 150 °C; <u>Fig. 6</u>		-	-	160	μA
Dynamic	characteristics					•	,
Q_r	recovered charge	ecovered charge $I_F = 6 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A}/\mu\text{s}$; $T_i = 25 \text{ °C}$; Fig. 7		-	9	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C		-	190	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C		-	30	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C		-	29	-	pF
E _{as}	non-repetitive avalanche energy	$I_R = 4.25 \text{ A}; T_{j(init)} = 25 \text{ °C}; L = 5 \text{ mH}$		45	-	-	mJ



 $V_o = 0.444 \text{ V}; R_s = 0.2192 \Omega$

(1) $T_i = -55$ °C; typical values

(2) T_i = 0 °C; typical values

(3) T_j = 25 °C; typical values (4) T_j = 100 °C; typical values

(5) T_i = 150 °C; typical values

(6) T_i = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

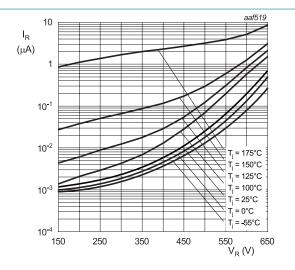


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

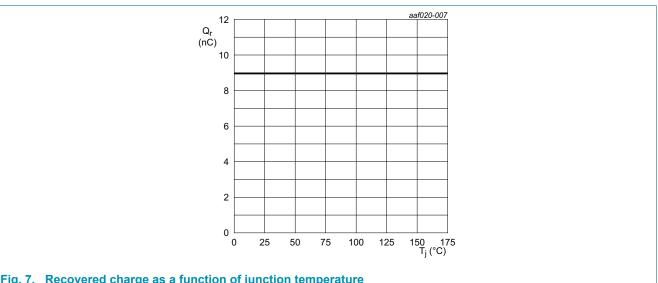
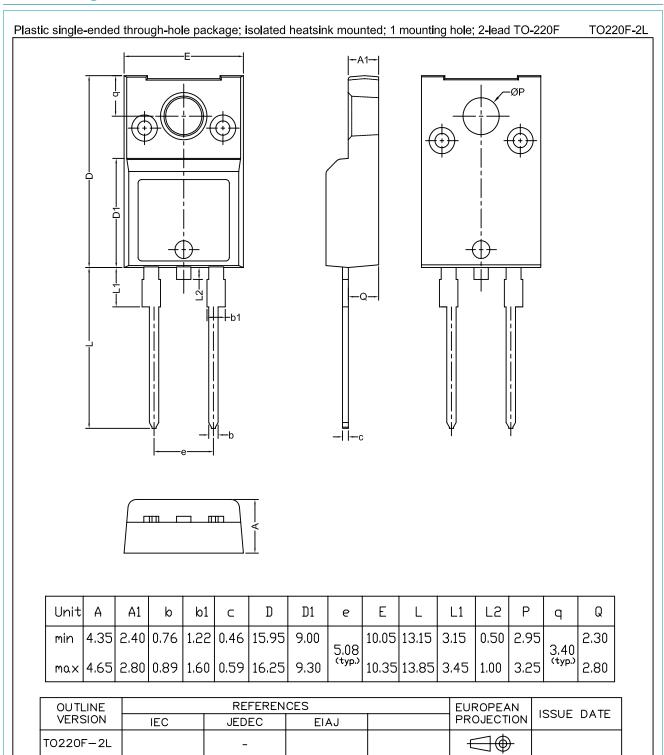


Fig. 7. Recovered charge as a function of junction temperature

12. Package outline



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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